

## AUTOMOTIVE N-Channel 40V 175°C MOSFET

### FEATURES

- AEC-Q101 Qualified
- 100% UIS and R<sub>g</sub> Tested
- 175°C Operating Junction Temperature
- Wettable Flank Package
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

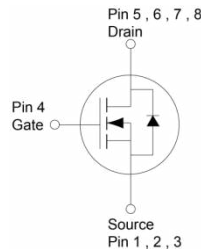
### APPLICATIONS

- 12V Automotive Systems
- Solenoid and Motor Control
- Automotive Transmission Control
- DC-DC Converters

| PRODUCT SUMMARY           |                       |      |
|---------------------------|-----------------------|------|
| PARAMETER                 | VALUE                 | UNIT |
| V <sub>DS</sub>           | 40                    | V    |
| R <sub>DS(on)</sub> (max) | V <sub>GS</sub> = 10V | 3.3  |
|                           | V <sub>GS</sub> = 7V  | 5.1  |
| Q <sub>g</sub>            | 87                    | nC   |



PDFN56U



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted) |                                   |                        |      |
|---|-----------------------------------|------------------------|------|
| PARAMETER   | SYMBOL                            | LIMIT                  | UNIT |
| Drain-Source Voltage  | V <sub>DS</sub>                   | 40                     | V    |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ±20                    | V    |
| Continuous Drain Current (Note 1)                                       | I <sub>D</sub>                    | T <sub>C</sub> = 25°C  | 121  |
|   |                                   | T <sub>A</sub> = 25°C  | 21   |
| Pulsed Drain Current  | I <sub>DM</sub>                   | 484                    | A    |
| Single Pulse Avalanche Current (Note 2)                                 | I <sub>AS</sub>                   | 36                     | A    |
| Single Pulse Avalanche Energy (Note 2)                                  | E <sub>AS</sub>                   | 194                    | mJ   |
| Total Power Dissipation   | P <sub>D</sub>                    | T <sub>C</sub> = 25°C  | 107  |
|   |                                   | T <sub>C</sub> = 125°C | 36   |
| Total Power Dissipation   | P <sub>D</sub>                    | T <sub>A</sub> = 25°C  | 3.1  |
|   |                                   | T <sub>A</sub> = 125°C | 1    |
| Operating Junction and Storage Temperature Range                        | T <sub>J</sub> , T <sub>STG</sub> | - 55 to +175           | °C   |

| THERMAL RESISTANCE                       |                  |         |      |
|--|------------------|---------|------|
| PARAMETER                                | SYMBOL           | MAXIMUM | UNIT |
| Thermal Resistance – Junction to Case    | R <sub>θJC</sub> | 1.4     | °C/W |
| Thermal Resistance – Junction to Ambient | R <sub>θJA</sub> | 48      | °C/W |

**Thermal Performance Note:** R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design. The R<sub>θJA</sub> limit presented here is based on mounting on a 1 in<sup>2</sup> pad of 2 oz copper.

| <b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted) |  |              |     |      |           |               |
|--|--|--------------|-----|------|-----------|---------------|
| PARAMETER  | CONDITIONS   | SYMBOL       | MIN | TYP  | MAX       | UNIT          |
| <b>Static</b>  |  |              |     |      |           |               |
| Drain-Source Breakdown Voltage   | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$                                       | $BV_{DSS}$   | 40  | --   | --        | V             |
| Gate Threshold Voltage   | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$  | $V_{GS(TH)}$ | 1.8 | 2.5  | 3.8       | V             |
| Gate-Source Leakage Current  | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$                                    | $I_{GSS}$    | --  | --   | $\pm 100$ | nA            |
| Drain-Source Leakage Current   | $V_{GS} = 0\text{V}, V_{DS} = 40\text{V}$  | $I_{DSS}$    | --  | --   | 1         | $\mu\text{A}$ |
|  | $V_{GS} = 0\text{V}, V_{DS} = 40\text{V}$<br>$T_J = 125^\circ\text{C}$           |              | --  | --   | 100       |               |
|  | $V_{GS} = 0\text{V}, V_{DS} = 40\text{V}$<br>$T_J = 175^\circ\text{C}$           |              | --  | --   | 500       |               |
| Drain-Source On-State Resistance<br>(Note 3)   | $V_{GS} = 10\text{V}, I_D = 21\text{A}$  | $R_{DS(on)}$ | --  | 2.2  | 3.3       | m $\Omega$    |
|  | $V_{GS} = 10\text{V}, I_D = 21\text{A},$<br>$T_J = 125^\circ\text{C}$            |              | --  | 3.8  | 5.7       |               |
|  | $V_{GS} = 10\text{V}, I_D = 21\text{A},$<br>$T_J = 175^\circ\text{C}$            |              | --  | 4.8  | 7.3       |               |
|  | $V_{GS} = 7\text{V}, I_D = 17\text{A}$   |              | --  | 2.5  | 5.1       |               |
| Forward Transconductance (Note 3)  | $V_{DS} = 10\text{V}, I_D = 21\text{A}$  | $g_{fs}$     | --  | 68   | --        | S             |
| <b>Dynamic</b> (Note 4)  |  |              |     |      |           |               |
| Total Gate Charge  | $V_{GS} = 10\text{V}, V_{DS} = 20\text{V},$<br>$I_D = 21\text{A}$                | $Q_g$        | --  | 87   | --        | nC            |
| Total Gate Charge  | $V_{GS} = 7\text{V}, V_{DS} = 20\text{V},$<br>$I_D = 17\text{A}$                 | $Q_g$        | --  | 64   | --        |               |
| Gate-Source Charge   |  | $Q_{gs}$     | --  | 20   | --        |               |
| Gate-Drain Charge  |  | $Q_{gd}$     | --  | 23   | --        |               |
| Input Capacitance  | $V_{GS} = 0\text{V}, V_{DS} = 20\text{V},$<br>$f = 1.0\text{MHz}$                | $C_{iss}$    | --  | 4917 | --        | pF            |
| Output Capacitance   |  | $C_{oss}$    | --  | 484  | --        |               |
| Reverse Transfer Capacitance   |  | $C_{rss}$    | --  | 276  | --        |               |
| Gate Resistance  | $f = 1.0\text{MHz}$  | $R_g$        | 0.5 | 1.7  | 3.4       | $\Omega$      |
| <b>Switching</b> (Note 4)  |  |              |     |      |           |               |
| Turn-On Delay Time   | $V_{GS} = 10\text{V}, V_{DS} = 20\text{V},$<br>$I_D = 21\text{A}, R_G = 2\Omega$ | $t_{d(on)}$  | --  | 10   | --        | ns            |
| Rise Time  |  | $t_r$        | --  | 24   | --        |               |
| Turn-Off Delay Time  |  | $t_{d(off)}$ | --  | 49   | --        |               |
| Fall Time  |  | $t_f$        | --  | 23   | --        |               |
| <b>Source-Drain Diode</b>  |  |              |     |      |           |               |
| Diode Forward Voltage (Note 3)   | $V_{GS} = 0\text{V}, I_S = 21\text{A}$   | $V_{SD}$     | --  | --   | 1         | V             |
| Reverse Recovery Time  | $I_S = 21\text{A},$<br>$di/dt = 100\text{A}/\mu\text{s}$                         | $t_{rr}$     | --  | 30   | --        | ns            |
| Reverse Recovery Charge  |  | $Q_{rr}$     | --  | 20   | --        | nC            |

**Notes:**

1. Silicon limited current only.
2.  $L = 0.3\text{mH}, V_{GS} = 10\text{V}, V_{DD} = 25\text{V}, R_G = 50\Omega, I_{AS} = 36\text{A}$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse test: Pulse Width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
4. Switching time is essentially independent of operating temperature.

**ORDERING INFORMATION**

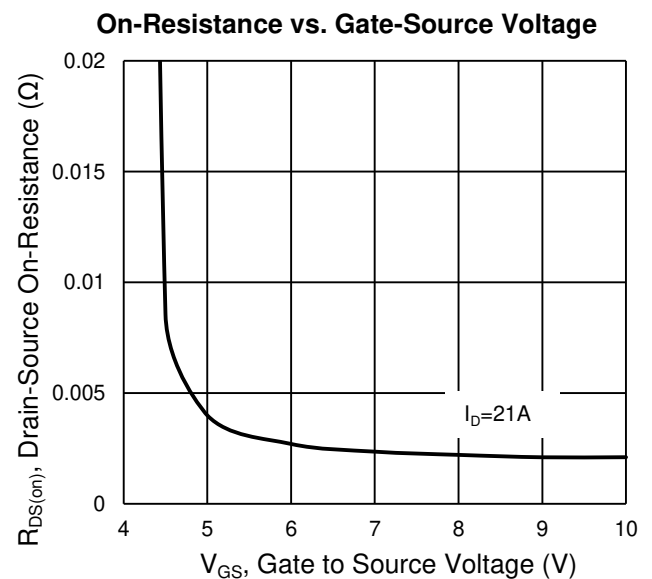
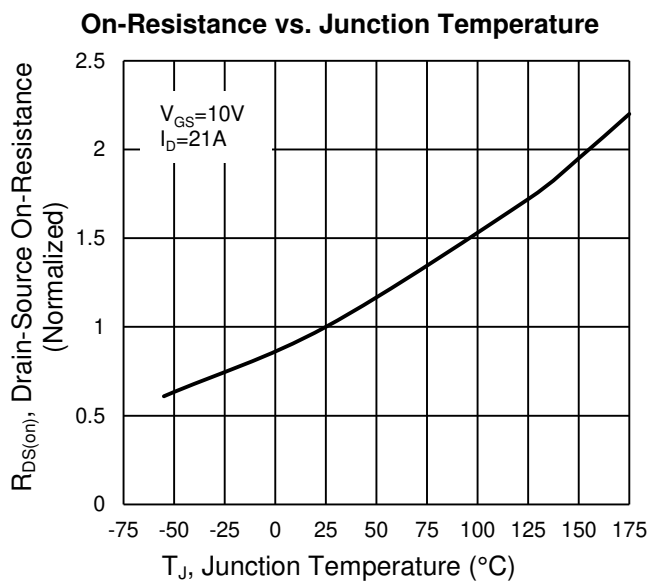
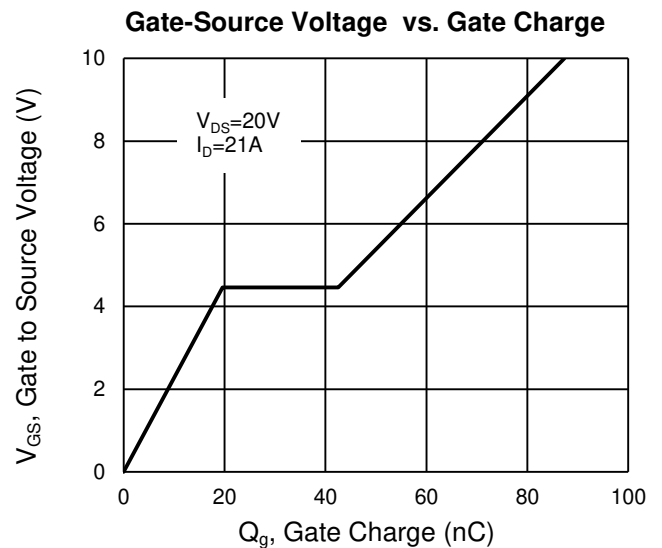
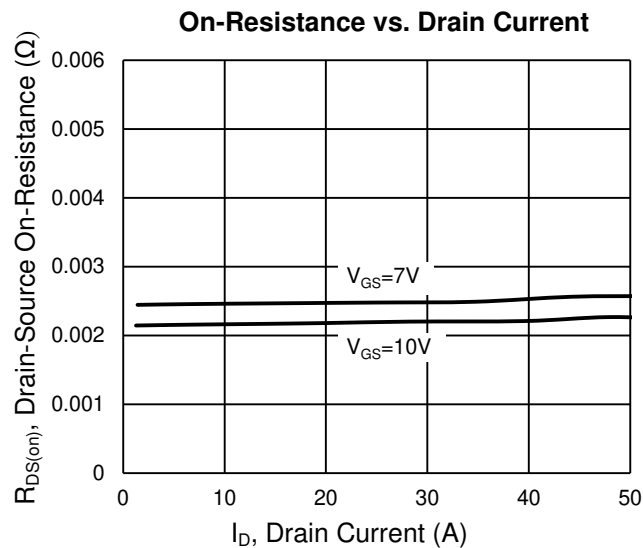
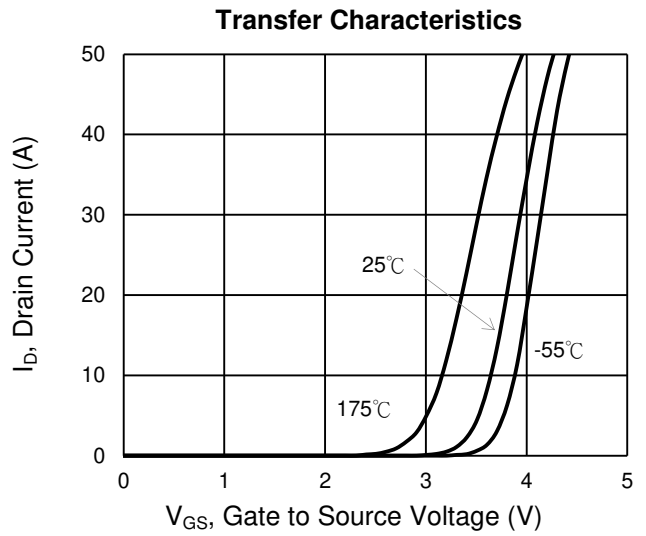
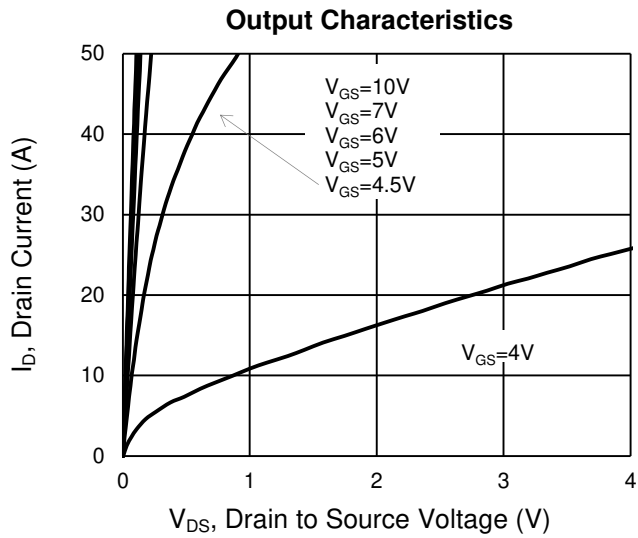
| ORDERING CODE      | PACKAGE | PACKING             |
|--------------------|---------|---------------------|
| TQM033NB04CR RLG   | PDFN56U | 2,500pcs / 13" Reel |
| TQM033NB04CR-V RLG | PDFN56U | 2,500pcs / 13" Reel |

**Notes:**

V : HOT test

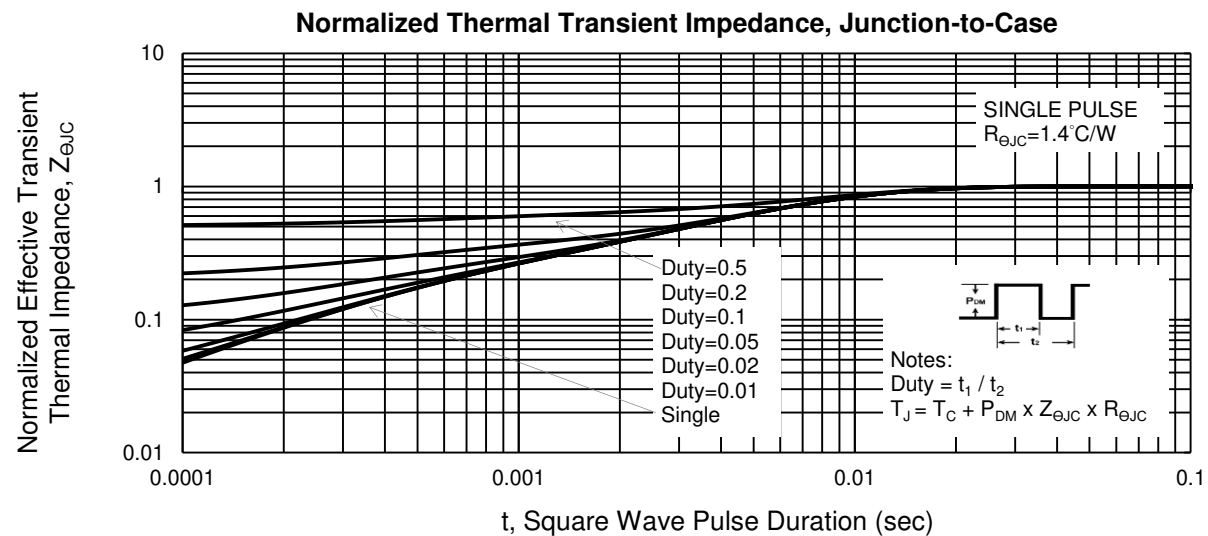
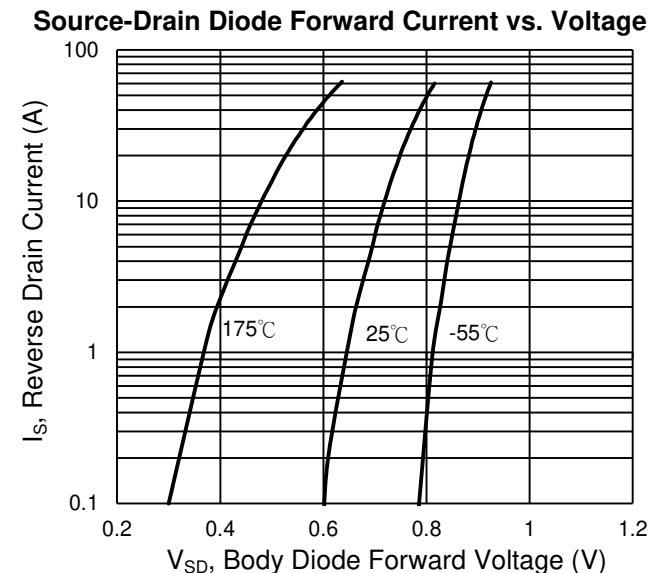
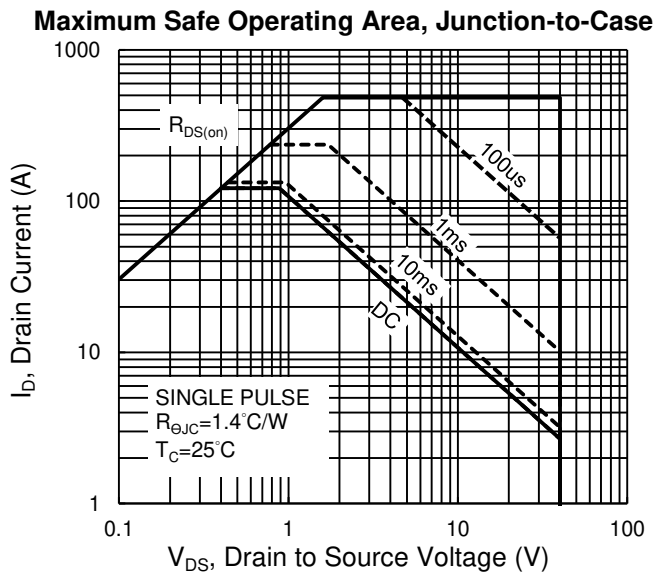
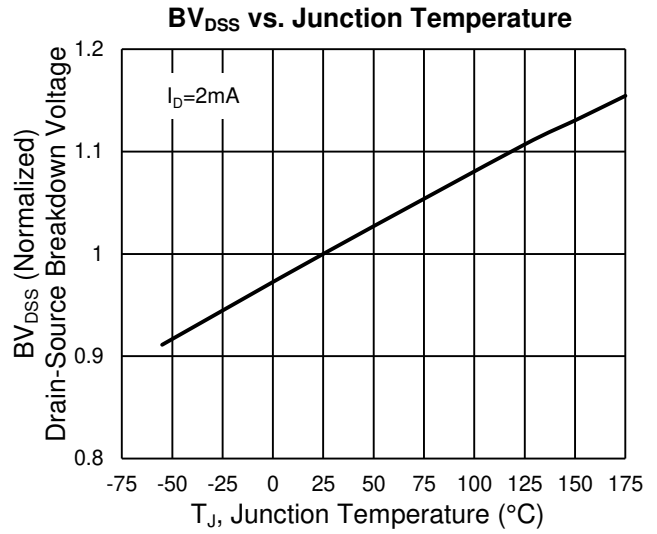
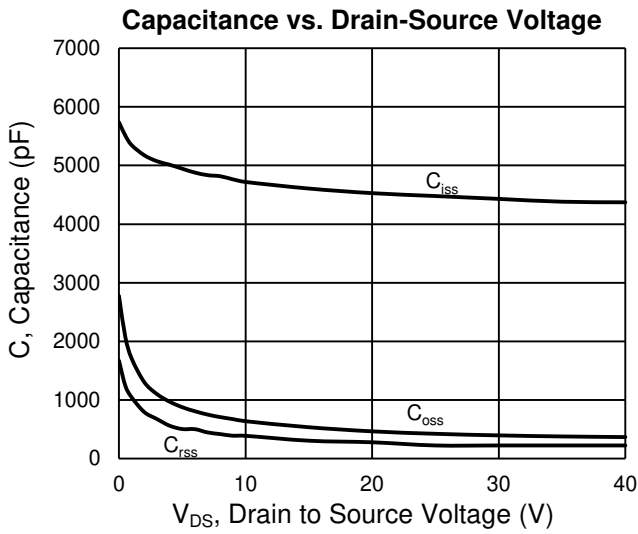
**CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)



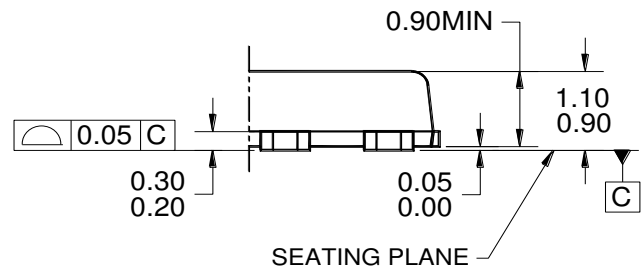
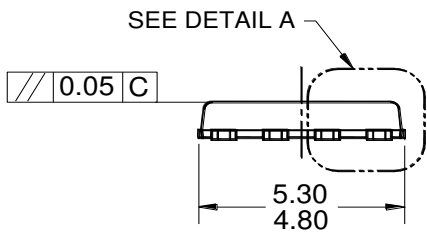
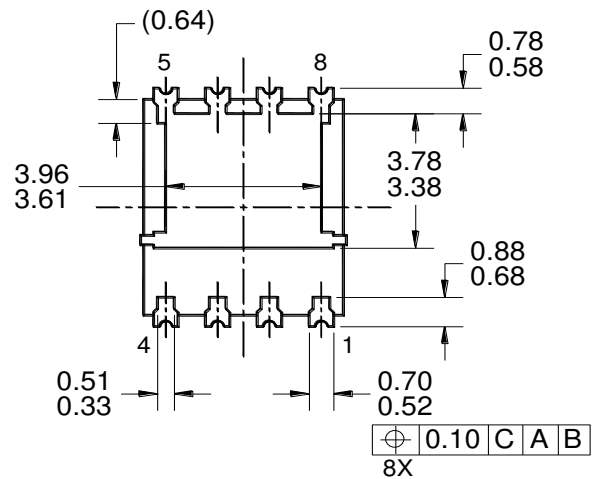
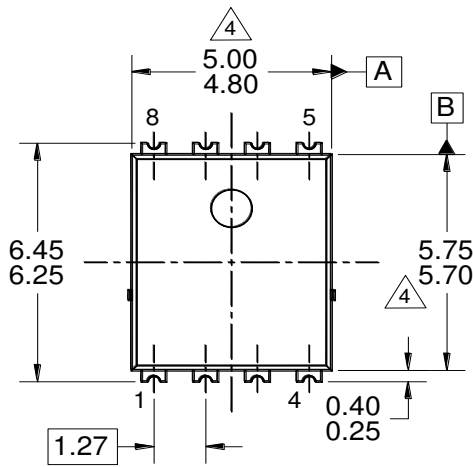
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( $T_A = 25^\circ\text{C}$  unless otherwise noted)

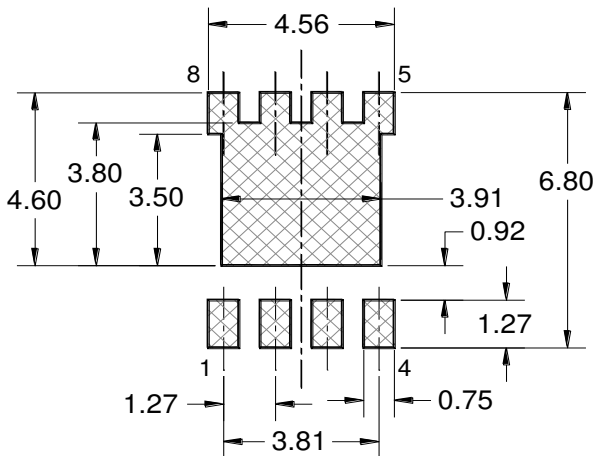


**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

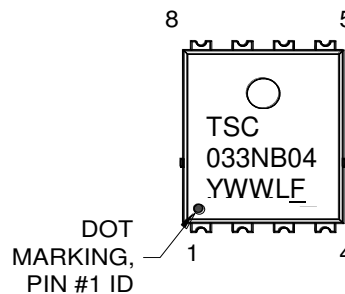
PDFN56U



DETAIL A  
(SCALE 2:1)



SUGGESTED PAD LAYOUT



MARKING DIAGRAM

NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: JEITA ED-7500B, EIAJ SC-111BB.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-PDFN56U-023 REV A.

- P/N = MARKING CODE  
 Y = YEAR CODE  
 WW = WEEK CODE (01~52)  
 L = LOT CODE (1~9, A~Z)  
 F = FACTORY CODE  
 - = AEC-Q101 QUALIFIED

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